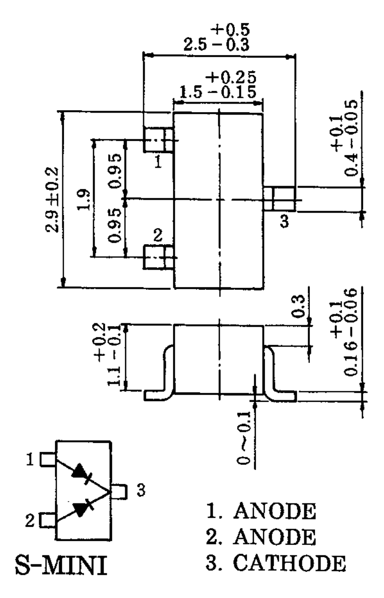
TOSHIBA Diode Silicon Epitaxial Planar Type

1SS337

Ultra High Speed Switching Application

Unit: mm



JEDEC	TD-236MOD
EIAJ	SC-59
TOSHIBA	1-3G1F

Weight: 0.012g

- Small package : SC-59
- Low forward voltage : $V_{F\ (3)} = 0.88V$ (typ.)
- Fast reverse recovery time : $t_{rr} = 6ns$ (typ.)
- Small total capacitance : $C_T = 1.6pF$ (typ.)

Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Maximum (peak) reverse voltage	V_{RM}	85	V
Reverse voltage	V_R	80	V
Maximum (peak) forward current	I_{FM}	600 *	mA
Average forward current	I_O	200 *	mA
Surge current (10ms)	I_{FSM}	6 *	A
Power dissipation	P	150	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	−55~150	°C

*: Unit rating. Total rating = unit rating × 1.5

Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Forward voltage	$V_{F\ (1)}$	—	I_F = 10mA	—	0.66	—	V
	$V_{F\ (2)}$	—	I_F = 100mA	—	0.80	—	
	$V_{F\ (3)}$	—	I_F = 200mA	—	0.88	1.20	
Reverse current	$I_{R\ (1)}$	—	V_R = 30V	—	—	0.25	μA
	$I_{R\ (2)}$	—	V_R = 80V	—	—	0.50	
Total capacitance	C_T	—	V_R = 0, f = 1MHz	—	1.6	—	pF
Reverse recovery time	t_{rr}	—	I_F = 30mA, Fig.1	—	6	20	ns